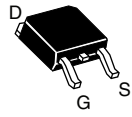


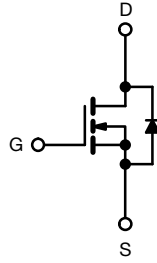
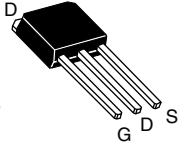


## Power MOSFET

DPAK (TO-252)



IPAK (TO-251)



N-Channel MOSFET

### FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Surface-mount (IRFR120, SiHFR120)
- Straight lead (IRFU120, SiHFU120)
- Available in tape and reel
- Fast switching
- Ease of paralleling
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



RoHS COMPLIANT HALOGEN FREE Available

### PRODUCT SUMMARY

V <sub>DS</sub> (V)	100	
R <sub>DS(on)</sub> (Ω)	V <sub>GS</sub> = 10 V	0.27
Q <sub>g</sub> max. (nC)	16	
Q <sub>gs</sub> (nC)	4.4	
Q <sub>gd</sub> (nC)	7.7	
Configuration	Single	

### DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness. The DPAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU, SiHFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 W are possible in typical surface mount applications.

### ORDERING INFORMATION

PACKAGE	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	IPAK (TO-251)
Lead (Pb)-free and halogen-free	SiHFR120-GE3	SiHFR120TR-GE3 <sup>a</sup>	SiHFR120TRR-GE3 <sup>a</sup>	SiHFR120TRL-GE3 <sup>a</sup>	SiHFU120-GE3
	IRFR120PbF-BE3 <sup>b</sup>	IRFR120TRPbF-BE3 <sup>ab</sup>	IRFR120TRRPbF-BE3 <sup>ab</sup>	IRFR120TRLPbF-BE3 <sup>ab</sup>	-
Lead (Pb)-free	IRFR120PbF	IRFR120TRPbF <sup>a</sup>	IRFR120TRRPbF <sup>a</sup>	IRFR120TRLPbF <sup>a</sup>	IRFU120PbF

#### Notes

- a. See device orientation
- b. "-BE3" denotes alternate manufacturing location

### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V <sub>DS</sub>	100	V
Gate-source voltage	V <sub>GS</sub>	± 20	
Continuous drain current	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	A
		T <sub>C</sub> = 100 °C	
Pulsed drain current <sup>a</sup>	I <sub>DM</sub>	31	W/°C
Linear derating factor		0.33	
Linear derating factor (PCB mount) <sup>e</sup>		0.020	
Single pulse avalanche energy <sup>b</sup>	E <sub>AS</sub>	210	mJ
Repetitive avalanche Current <sup>a</sup>	I <sub>AR</sub>	7.7	A
Repetitive avalanche Energy <sup>a</sup>	E <sub>AR</sub>	4.2	mJ
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	W
Maximum power dissipation (PCB mount) <sup>e</sup>		T <sub>A</sub> = 25 °C	
Peak diode recovery dV/dt <sup>c</sup>	dV/dt	5.5	V/ns
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering recommendations (peak temperature) <sup>d</sup>	for 10 s	260	

#### Notes

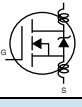

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. V<sub>DD</sub> = 25 V, starting T<sub>J</sub> = 25 °C, L = 5.3 mH, R<sub>g</sub> = 25 Ω, I<sub>AS</sub> = 7.7 A (see fig. 12).
- c. I<sub>SD</sub> ≤ 9.2 A, dI/dt ≤ 110 A/μs, V<sub>DD</sub> ≤ V<sub>DS</sub>, T<sub>J</sub> ≤ 150 °C.
- d. 1.6 mm from case.
- e. When mounted on 1" square PCB (FR-4 or G-10 material).



THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	-	110	°C/W
Maximum junction-to-ambient (PCB mount) <sup>a</sup>	$R_{thJA}$	-	-	50	
Maximum junction-to-case (drain)	$R_{thJC}$	-	-	3.0	

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		100	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$		-	0.13	-	V/°C
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	$\mu\text{A}$
		$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 4.6\text{ A}^b$	-	-	0.27	$\Omega$
Forward transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 4.6\text{ A}$		1.6	-	-	S
<b>Dynamic</b>							
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}, \text{ see fig. 5}$		-	360	-	pF
Output capacitance	$C_{oss}$			-	150	-	
Reverse transfer capacitance	$C_{rss}$			-	34	-	
Total gate charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 9.2\text{ A}, V_{DS} = 80\text{ V}, \text{ see fig. 6 and 13}^b$	-	-	16	nC
Gate-source charge	$Q_{gs}$			-	-	4.4	
Gate-drain charge	$Q_{gd}$			-	-	7.7	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, I_D = 9.2\text{ A}, R_g = 18\text{ }\Omega, R_D = 5.2\text{ }\Omega, \text{ see fig. 10}^b$		-	6.8	-	ns
Rise time	$t_r$			-	27	-	
Turn-off delay time	$t_{d(off)}$			-	18	-	
Fall time	$t_f$			-	17	-	
Internal drain inductance	$R_g$	$f = 1\text{ MHz}, \text{ open drain}$		1.0	-	5.0	$\Omega$
Internal source inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Input capacitance	$L_S$			-	7.5	-	
<b>Drain-source body diode characteristics</b>							
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	7.7	A
Pulsed diode forward current <sup>a</sup>	$I_{SM}$			-	-	31	
Body diode voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 7.7\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	2.5	V
Body diode reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 9.2\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	130	260	ns
Body diode reverse recovery charge	$Q_{rr}$			-	0.65	1.3	$\mu\text{C}$
Forward turn-on time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .



## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

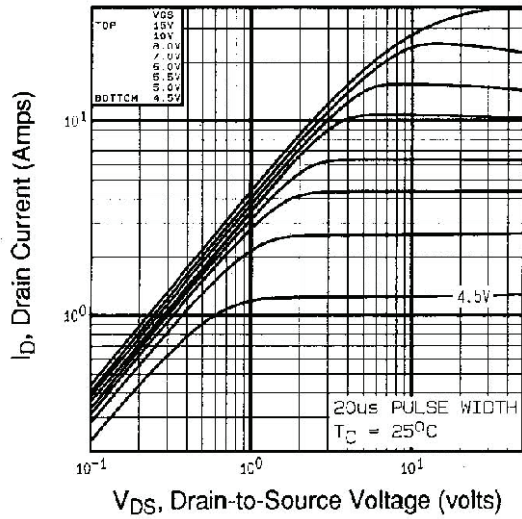


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$

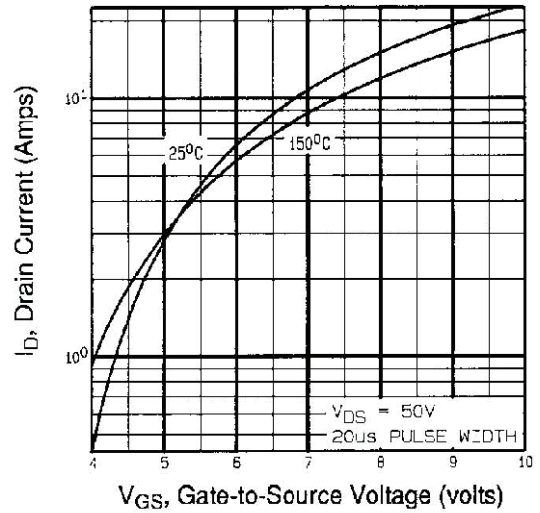


Fig. 3 - Typical Transfer Characteristics

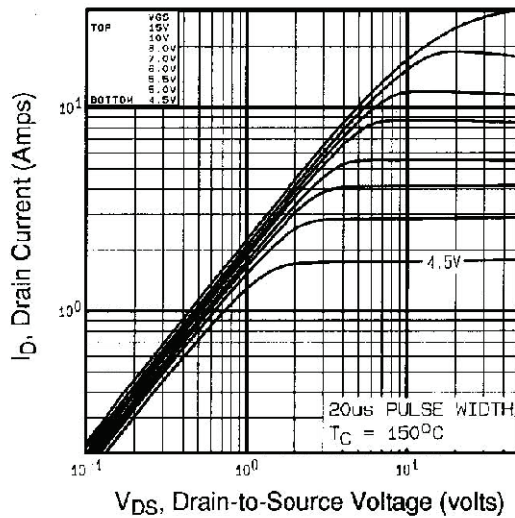


Fig. 2 - Typical Output Characteristics,  $T_C = 150\text{ }^\circ\text{C}$

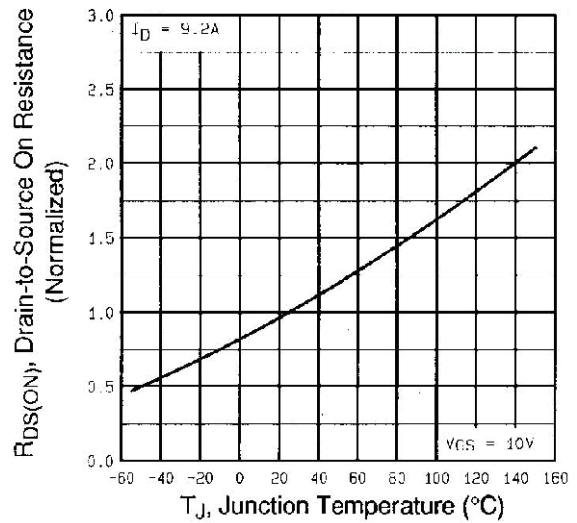


Fig. 4 - Normalized On-Resistance vs. Temperature

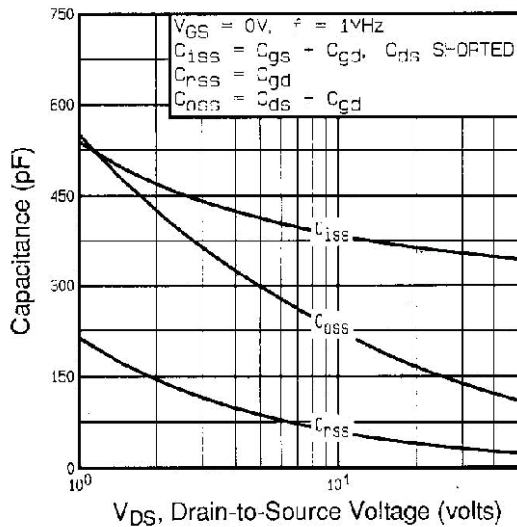


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

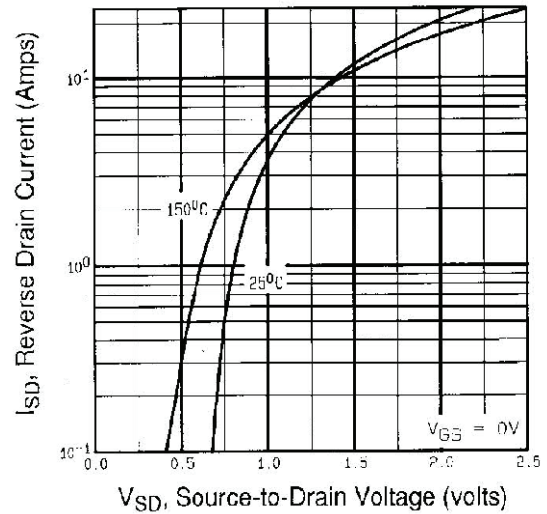


Fig. 7 - Typical Source-Drain Diode Forward Voltage

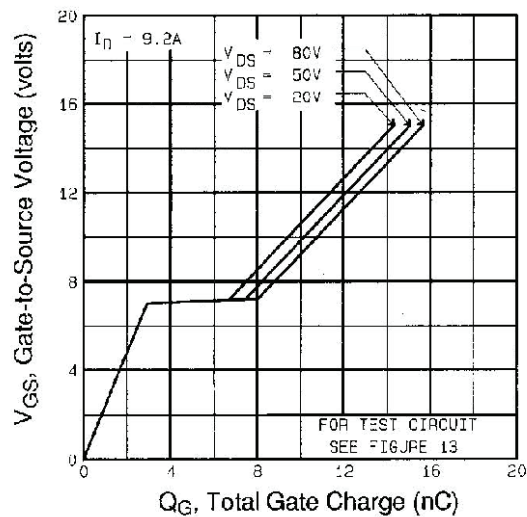


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

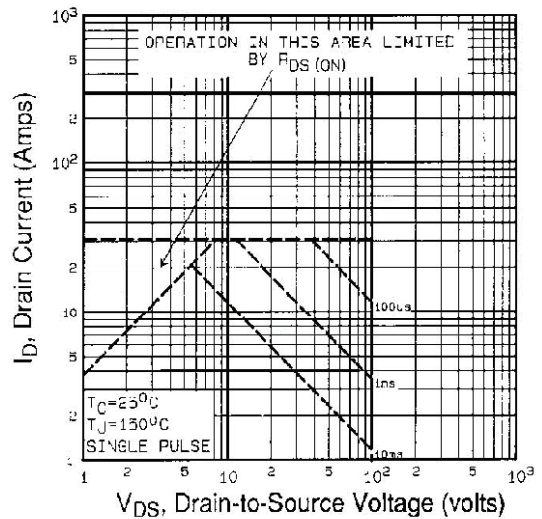


Fig. 8 - Maximum Safe Operating Area

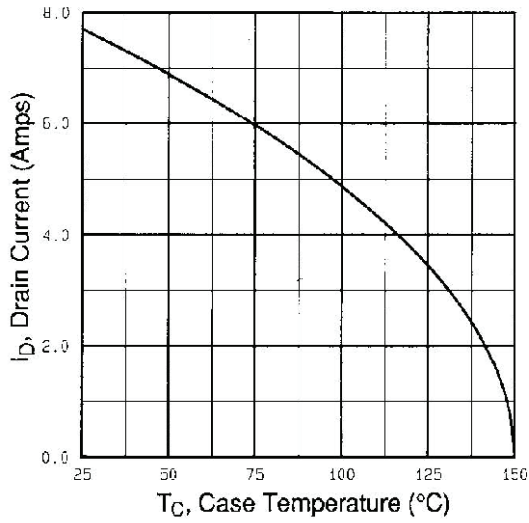


Fig. 9 - Maximum Drain Current vs. Case Temperature

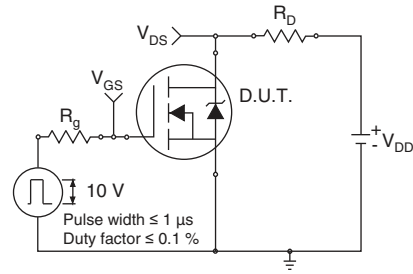


Fig. 10a - Switching Time Test Circuit

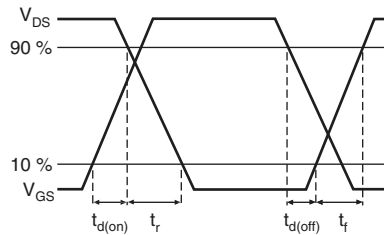


Fig. 10b - Switching Time Waveforms

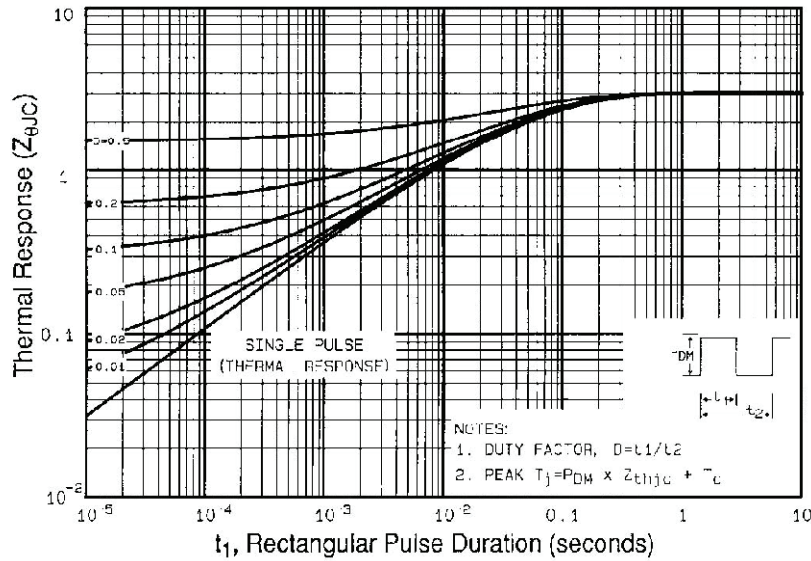


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

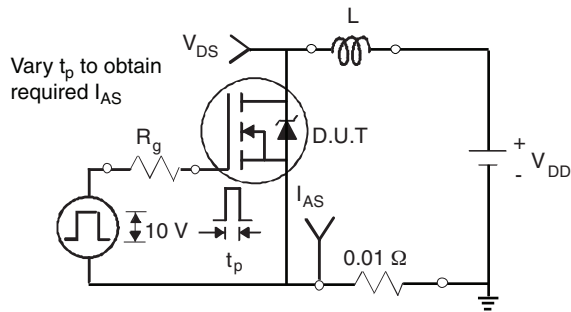


Fig. 12a - Unclamped Inductive Test Circuit



Fig. 12b - Unclamped Inductive Waveforms

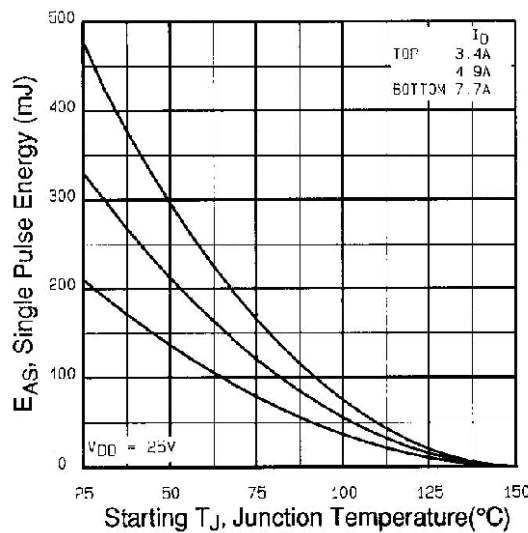


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

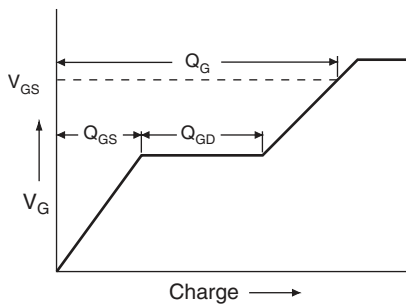


Fig. 13a - Basic Gate Charge Waveform

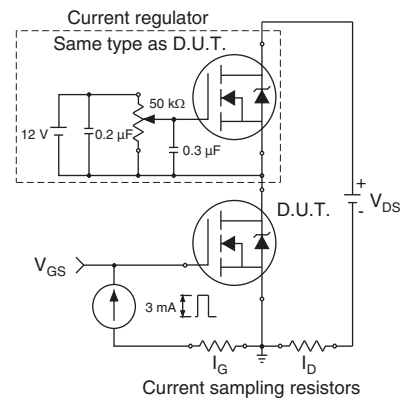
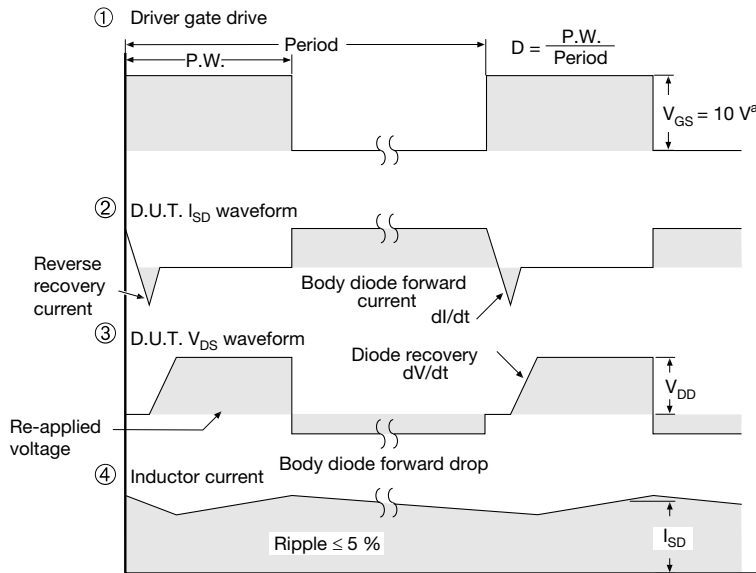
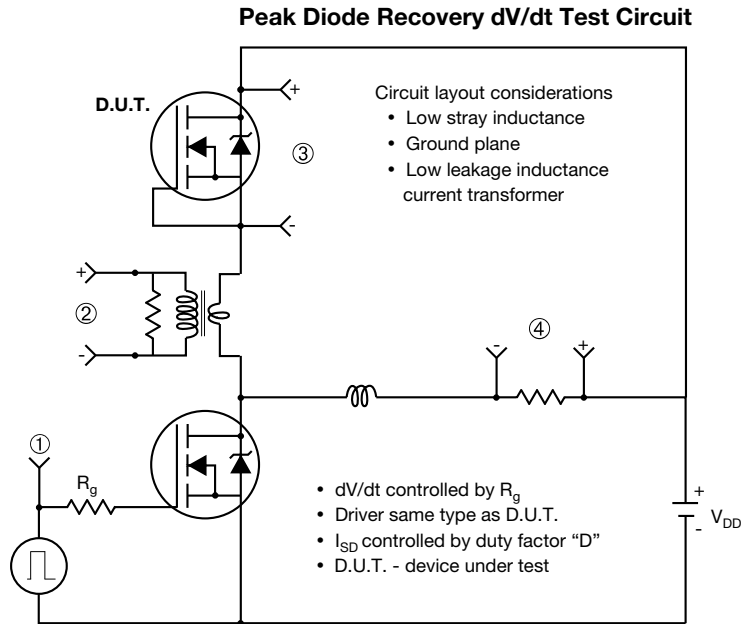


Fig. 13b - Gate Charge Test Circuit



**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

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# TO-252AA Case Outline

## VERSION 1: FACILITY CODE = Y



MILLIMETERS		
DIM.	MIN.	MAX.
A	2.18	2.38
A1	-	0.127
b	0.64	0.88
b2	0.76	1.14
b3	4.95	5.46
C	0.46	0.61
C2	0.46	0.89
D	5.97	6.22
D1	4.10	-
E	6.35	6.73
E1	4.32	-
H	9.40	10.41
e	2.28 BSC	
e1	4.56 BSC	
L	1.40	1.78
L3	0.89	1.27
L4	-	1.02
L5	1.01	1.52

### Note

- Dimension L3 is for reference only





VERSION 2: FACILITY CODE = N



MILLIMETERS		
DIM.	MIN.	MAX.
A	2.18	2.39
A1	-	0.13
b	0.65	0.89
b1	0.64	0.79
b2	0.76	1.13
b3	4.95	5.46
c	0.46	0.61
c1	0.41	0.56
c2	0.46	0.60
D	5.97	6.22
D1	5.21	-
E	6.35	6.73
E1	4.32	-
e	2.29 BSC	
H	9.94	10.34

MILLIMETERS		
DIM.	MIN.	MAX.
L	1.50	1.78
L1	2.74 ref.	
L2	0.51 BSC	
L3	0.89	1.27
L4	-	1.02
L5	1.14	1.49
L6	0.65	0.85
θ	0°	10°
θ1	0°	15°
θ2	25°	35°

Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022  
 DWG: 5347

### Case Outline for TO-251AA (High Voltage)

#### OPTION 1:



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	0.89	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b1	0.65	0.79	0.026	0.031
b2	0.76	1.14	0.030	0.045
b3	0.76	1.04	0.030	0.041
b4	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c1	0.41	0.56	0.016	0.022
c2	0.46	0.86	0.018	0.034
D	5.97	6.22	0.235	0.245

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
e	2.29 BSC		2.29 BSC	
L	8.89	9.65	0.350	0.380
L1	1.91	2.29	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.14	1.52	0.045	0.060
θ1	0'	15'	0'	15'
θ2	25'	35'	25'	35'

ECN: E21-0682-Rev. C, 27-Dec-2021  
DWG: 5968

#### Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- Dimension are shown in inches and millimeters
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.13 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- Thermal pad contour optional with dimensions b4, L2, E1 and D1
- Lead dimension uncontrolled in L3
- Dimension b1, b3 and c1 apply to base metal only
- Outline conforms to JEDEC® outline TO-251AA



**OPTION 2: FACILITY CODE = N**



DIM.	MIN.	NOM.	MAX.
A	2.180	2.285	2.390
A1	0.890	1.015	1.140
b	0.640	0.765	0.890
b1	0.640	0.715	0.790
b2	0.760	0.950	1.140
b3	0.760	0.900	1.040
b4	4.950	5.205	5.460
c	0.460	-	0.610
c1	0.410	-	0.560
c2	0.460	-	0.610
D	5.970	6.095	6.220
D1	4.300	-	-

DIM.	MIN.	NOM.	MAX.
D2	5.380	-	-
E	6.350	6.540	6.730
E1	4.32	-	-
e	2.29 BSC		
L	8.890	9.270	9.650
L1	1.910	2.100	2.290
L2	0.890	1.080	1.270
L3	1.140	1.330	1.520
L4	1.300	1.400	1.500
$\theta_1$	0°	7.5°	15°
$\theta_2$	4°	-	-

ECN: E21-0682-Rev. C, 27-Dec-2021  
DWG: 5968

**Notes**

- Dimensioning and tolerancing per ASME Y14.5M-1994
- All dimension are in millimeters, angles are in degrees
- Heat sink side flash is max. 0.8 mm

## RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)



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